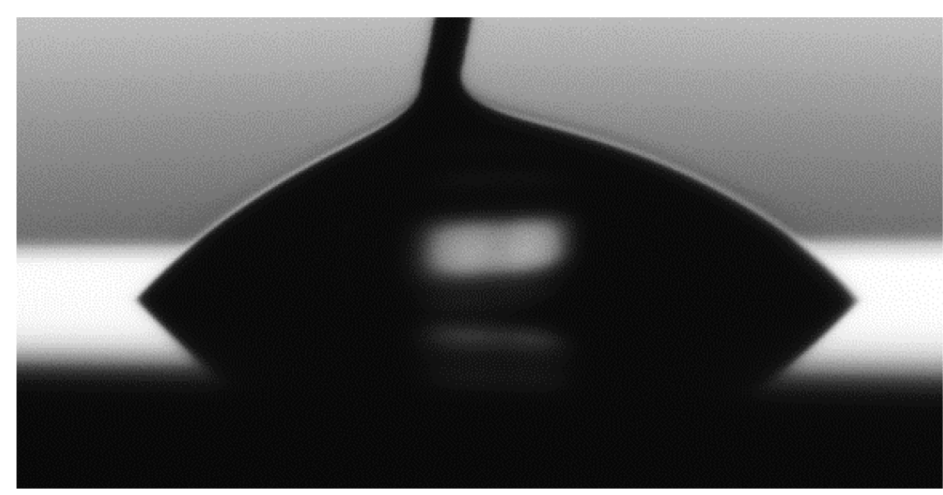
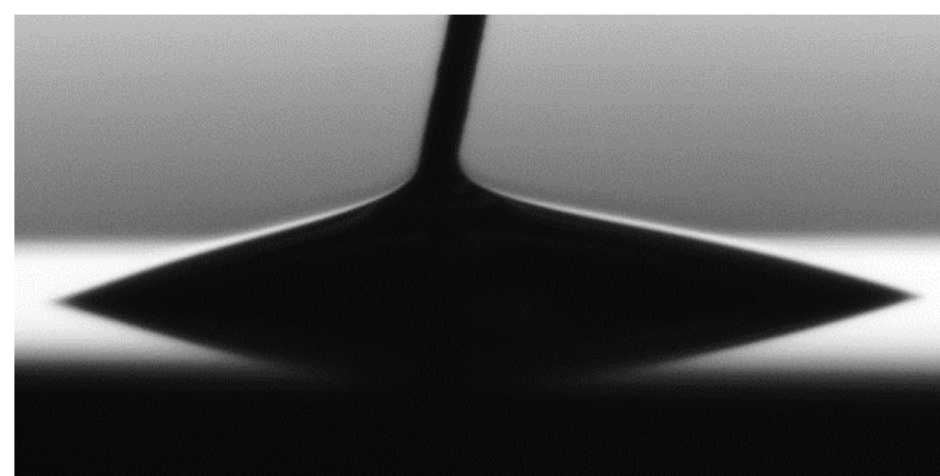


Electrowetting

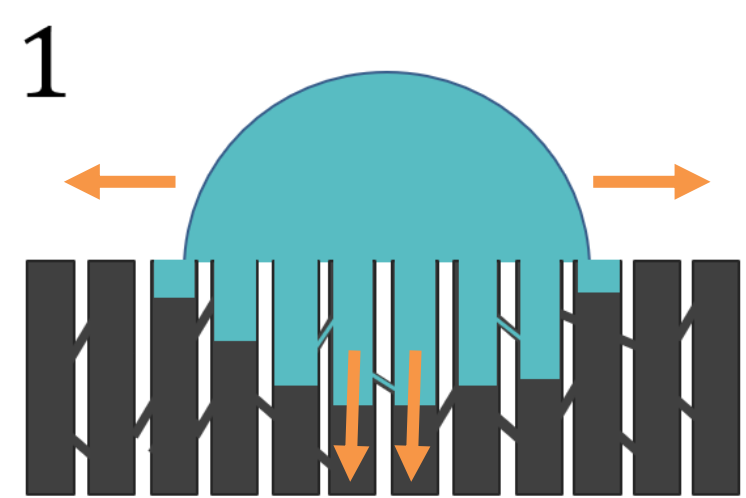


ΔV

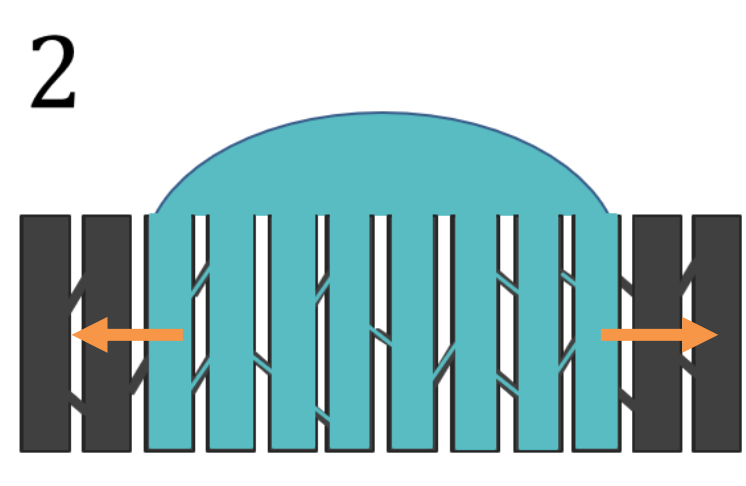


Change in the wetting properties due to an electric field.
Experimental images of NaCl solution on silicon.

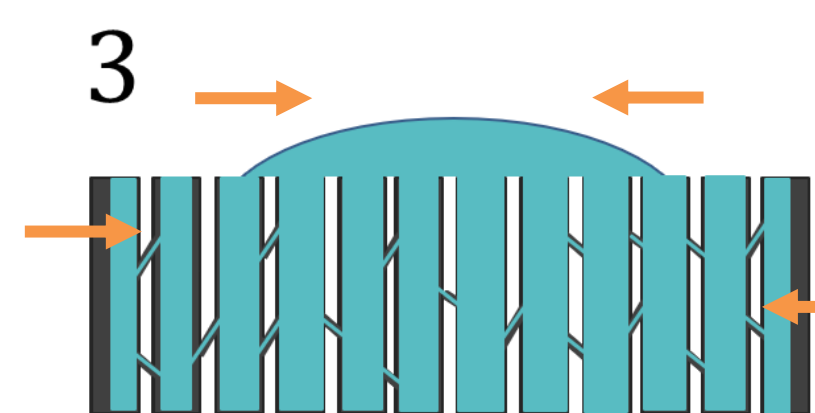
Spreading and radial imbibition at nanoporous silicon surfaces



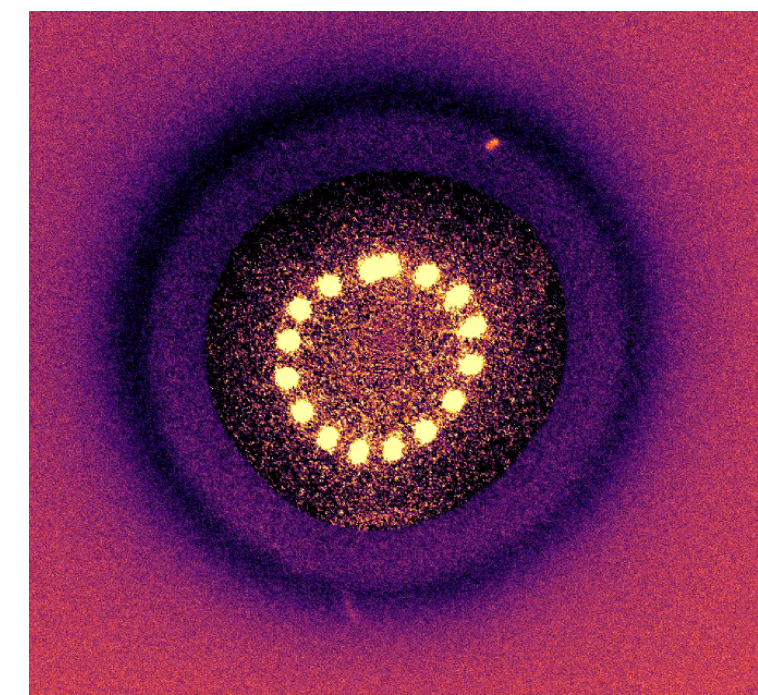
Spreading and vertical imbibition



Contact line pinning and radial imbibition



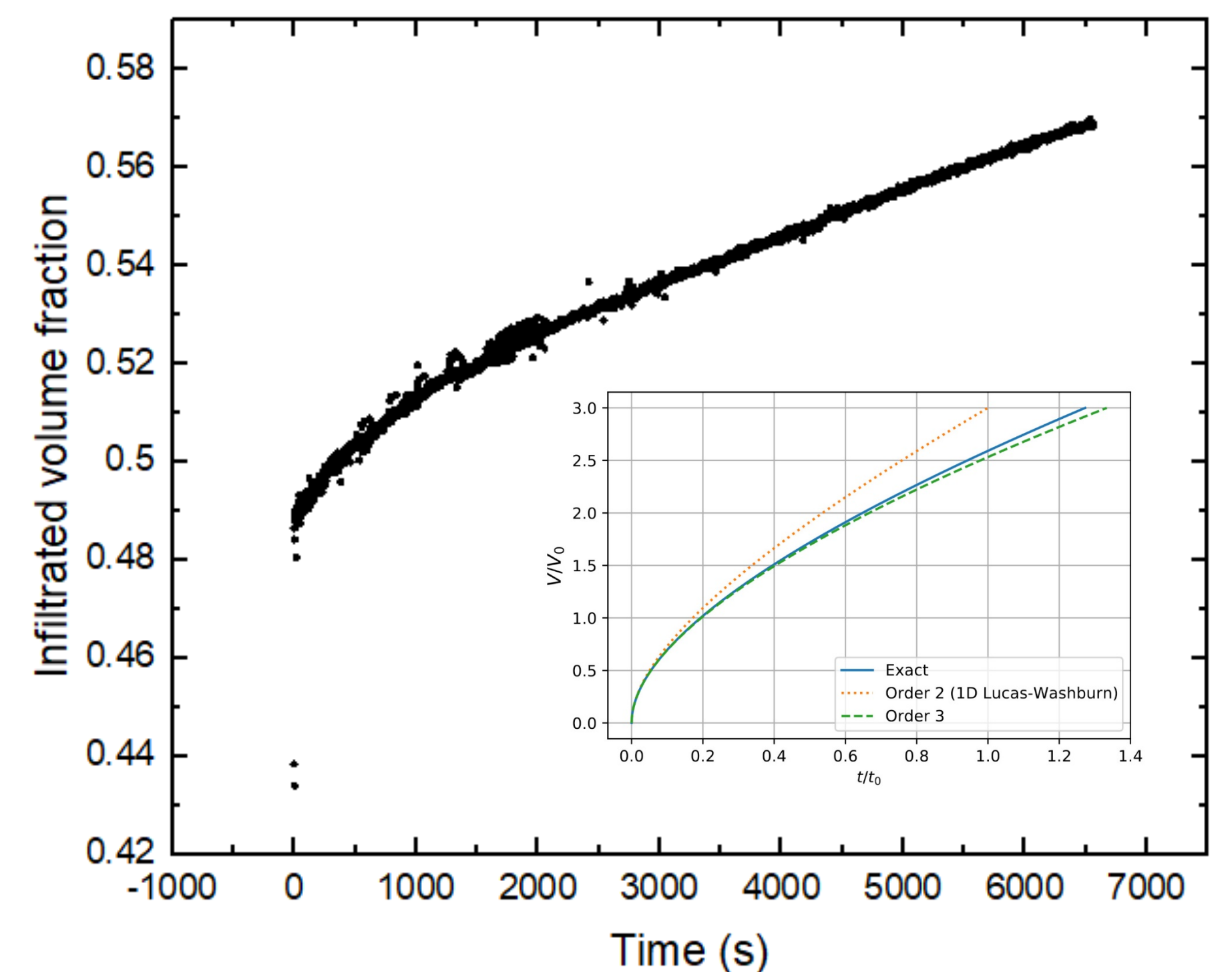
Receding of the imbibition front and contact line



Experimental top view of water on a pSi substrate.

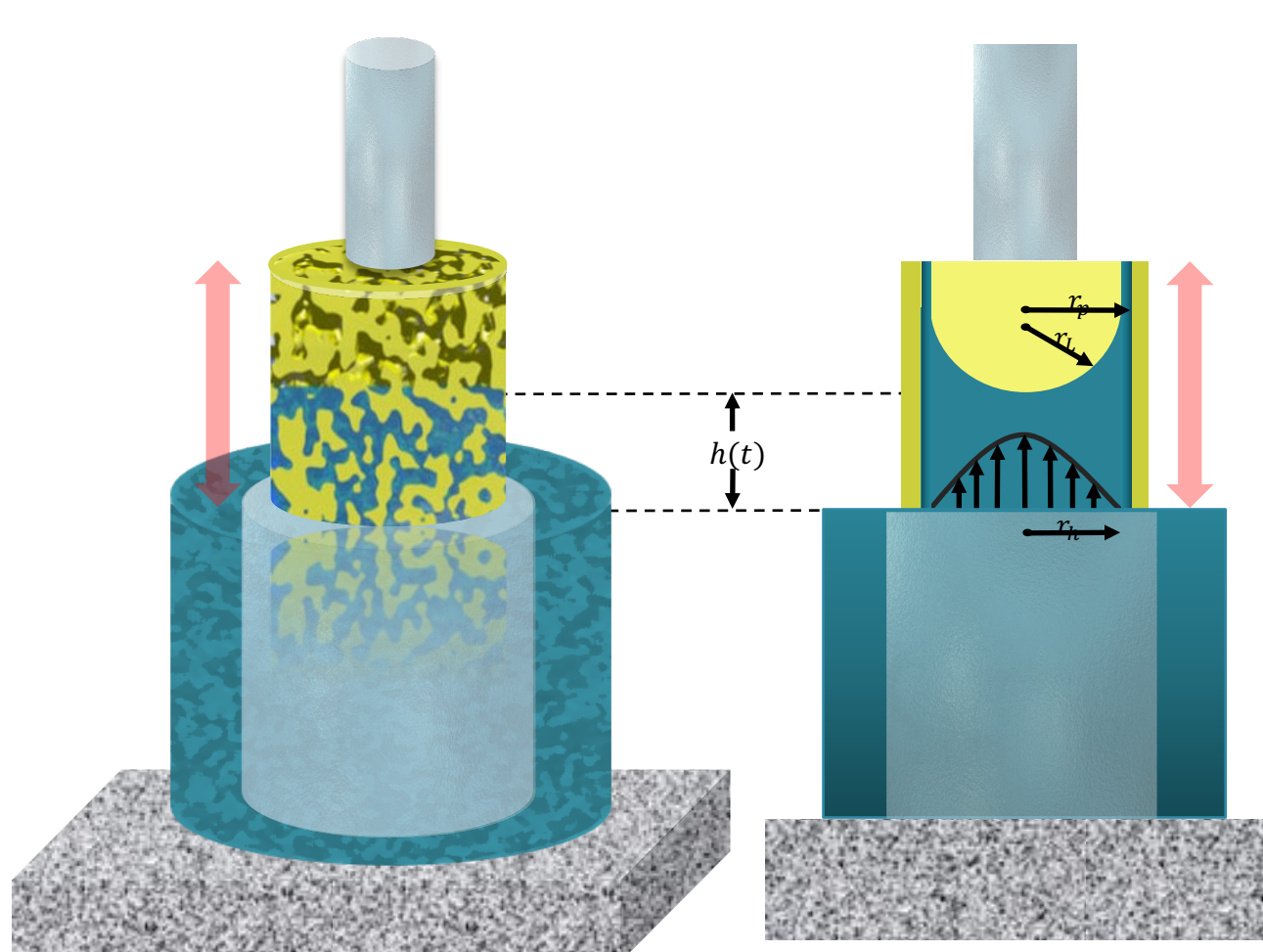
From Darcy's law, radial imbibition equation (1):

$$-\frac{2\kappa\Delta P}{\phi}t = r^2 \ln\left(\frac{r}{r_0}\right) + \frac{r_0^2 - r^2}{2}$$

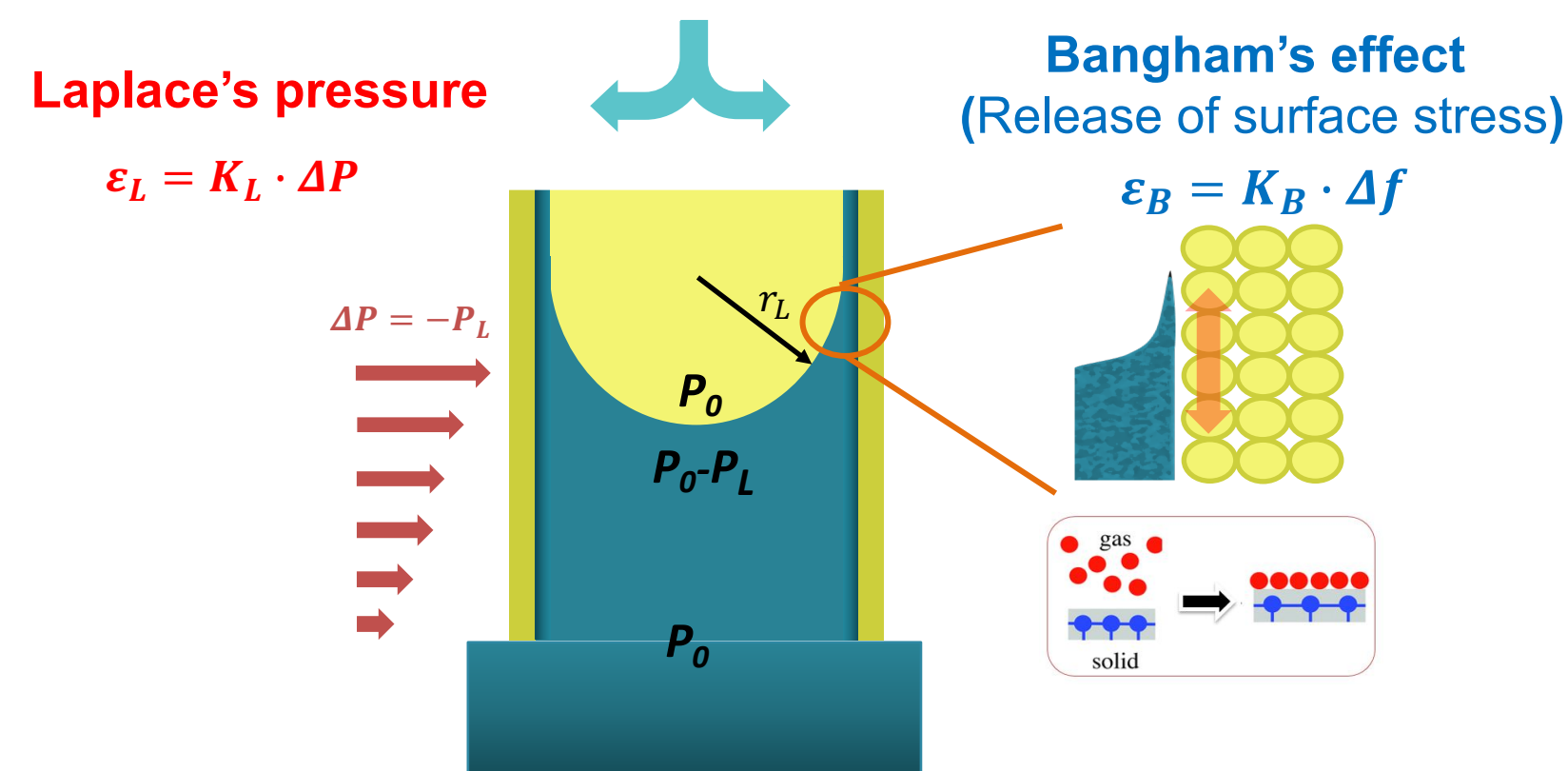


Experimental curve (squalane) and theoretical behavior according to model.

Dilatometry experiment upon imbibition



Interplay of strain (ϵ) inducing phenomena

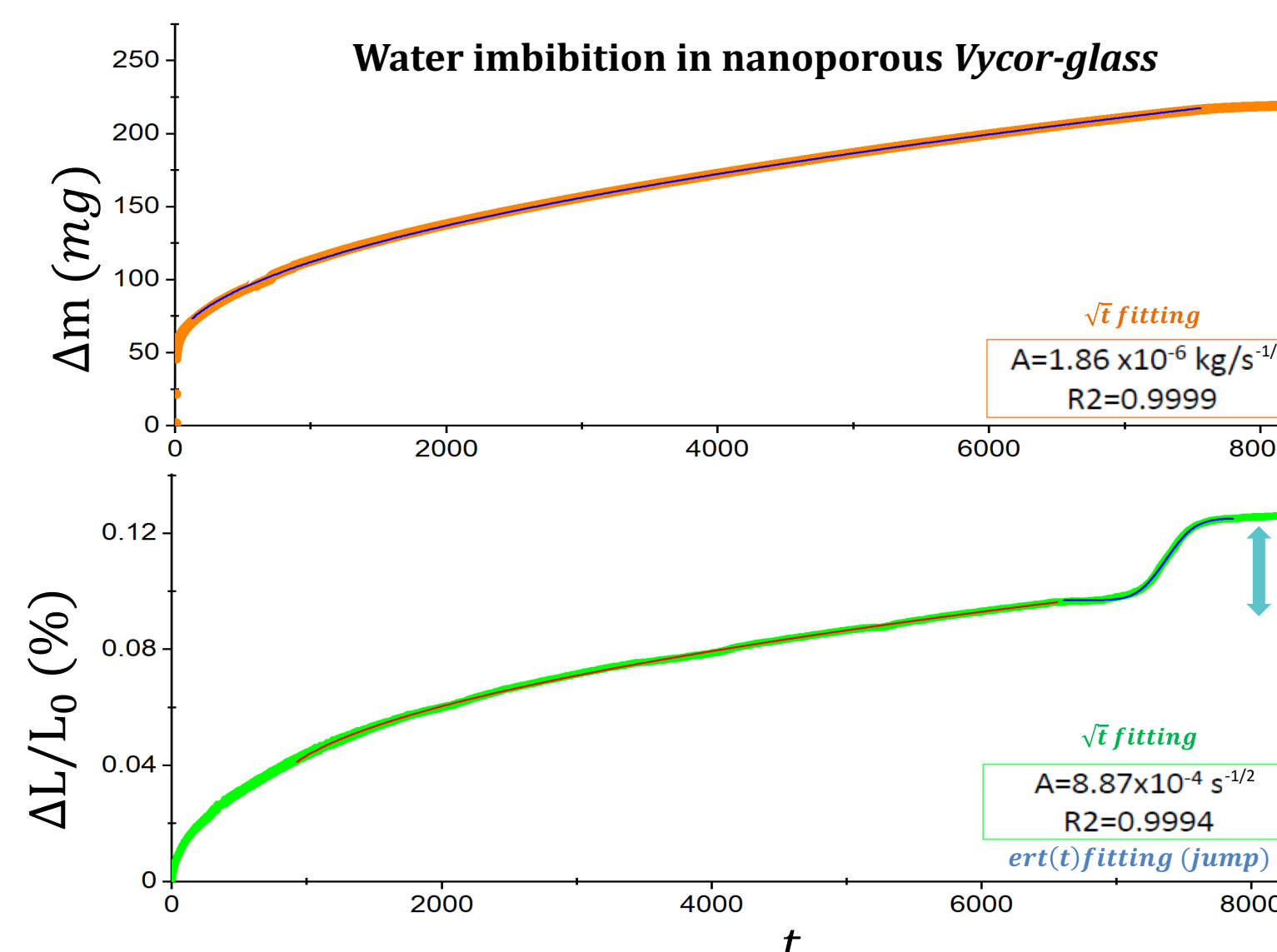
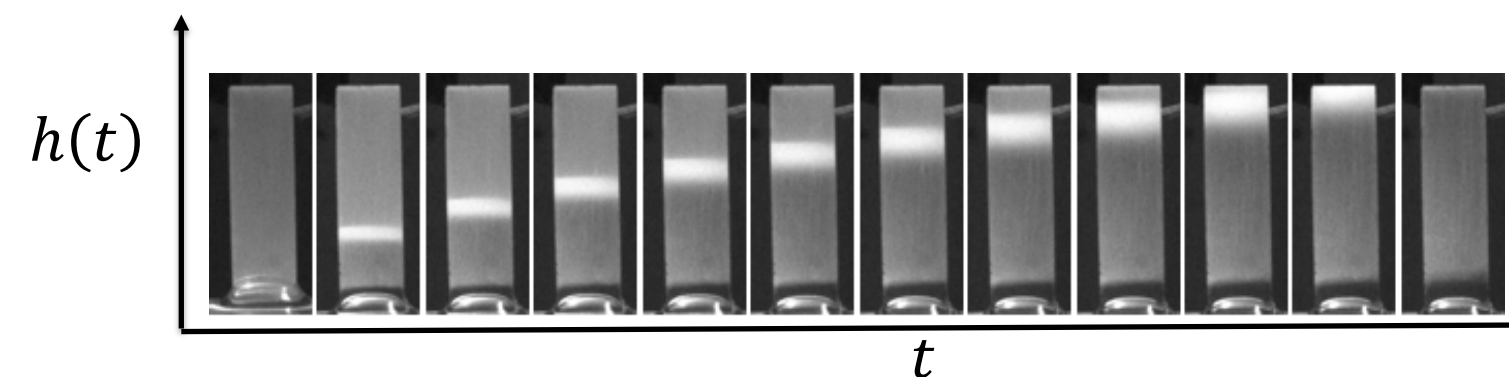


Imbibition-induced deformation of nanoporous media

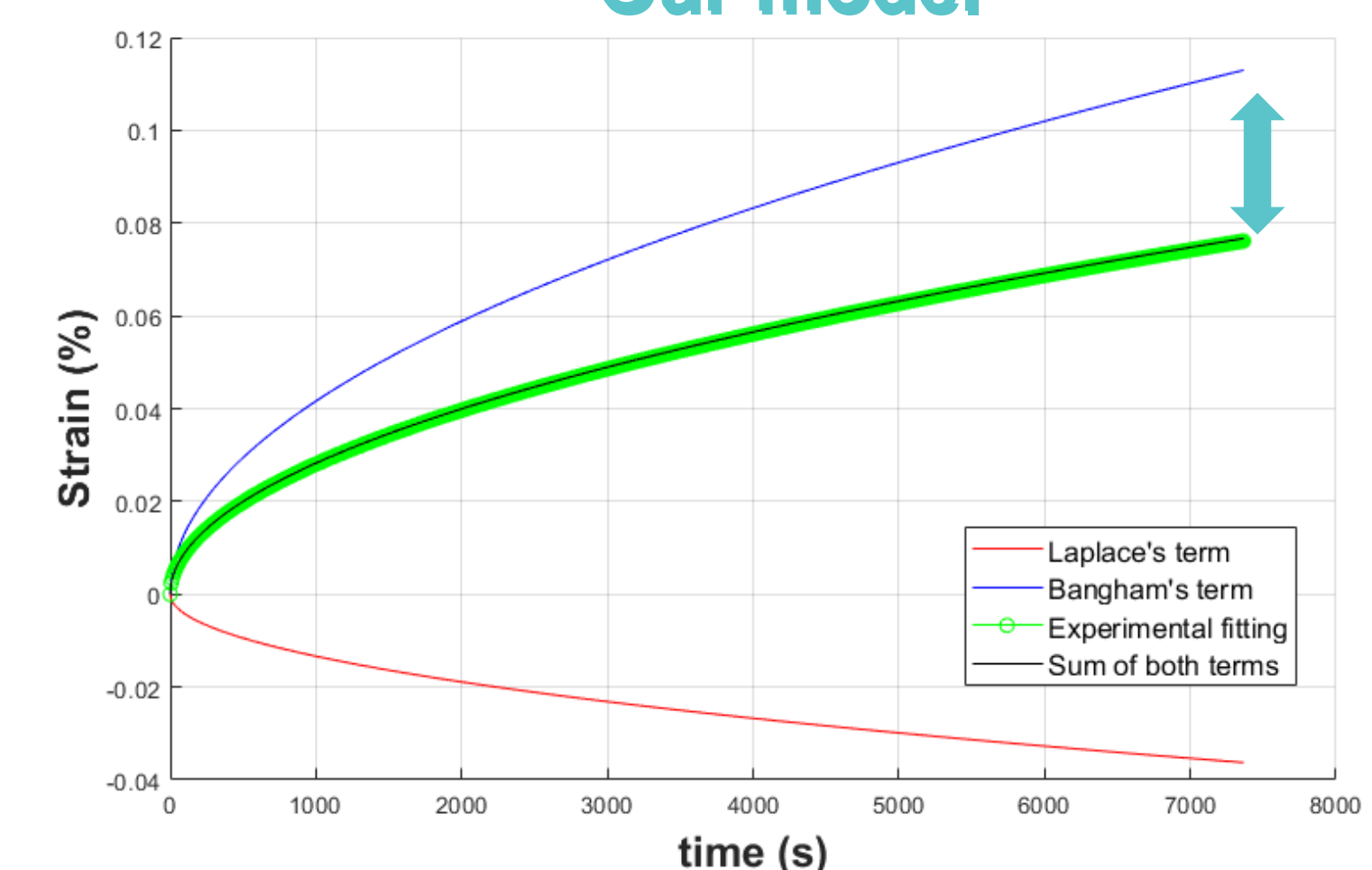
Experimental results

Capillary rise $h(t)$ follows the Lucas-Washburn law:

$$h(t) \propto \sqrt{t}$$



Our model



The released surface stress $\delta f(t)$ must be proportional to the "amount of wetted surface"

$$[\epsilon(t)]_B = \frac{2}{3K} \frac{v-1}{1-\phi} \frac{\delta f(t)}{r} \quad \delta f(t) \propto S(t)_{\text{wetted}} = C \times A \times \alpha \times h(t)$$

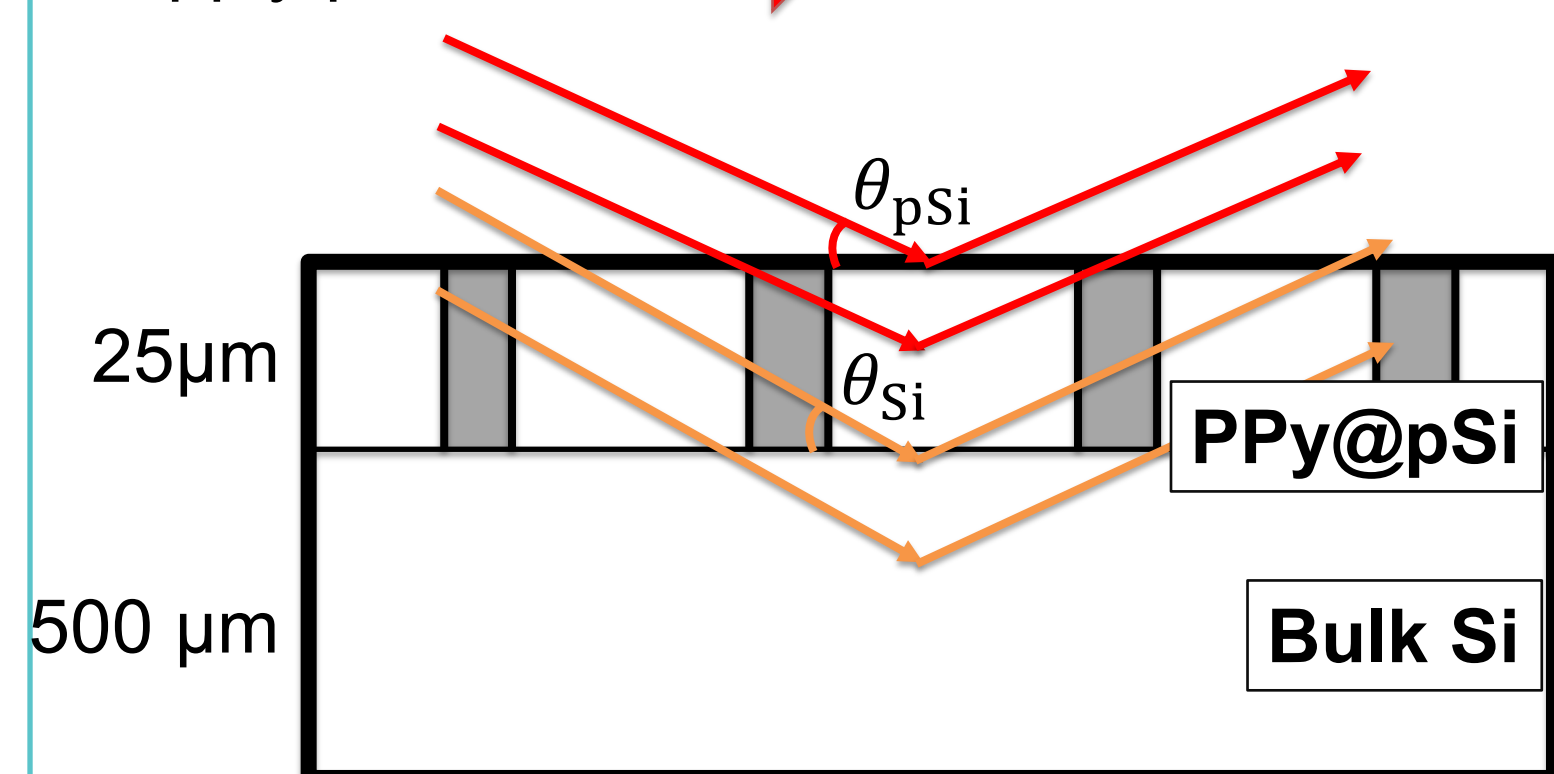
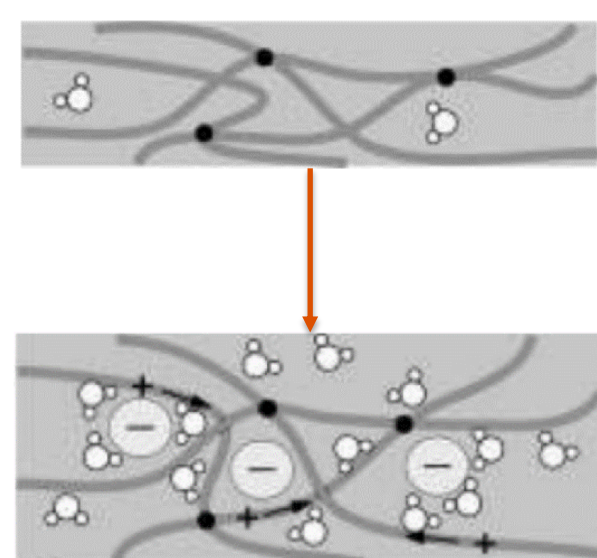
At a given time t , only the proportional part of the body $h(t)$ is under the Laplace pressure influence

$$[\epsilon(t)]_L = -\frac{\gamma}{r M_{PL}} \times \frac{h(t)}{L}$$

$$\epsilon(t) = [\epsilon(t)]_L + [\epsilon(t)]_B = \left[\left(-\frac{\gamma}{r M_{PL}} \times \frac{1}{L} \right) + \left(C \frac{4}{3K} \frac{v-1}{1-\phi} \frac{A}{r^2} \right) \right] \times h(t)$$

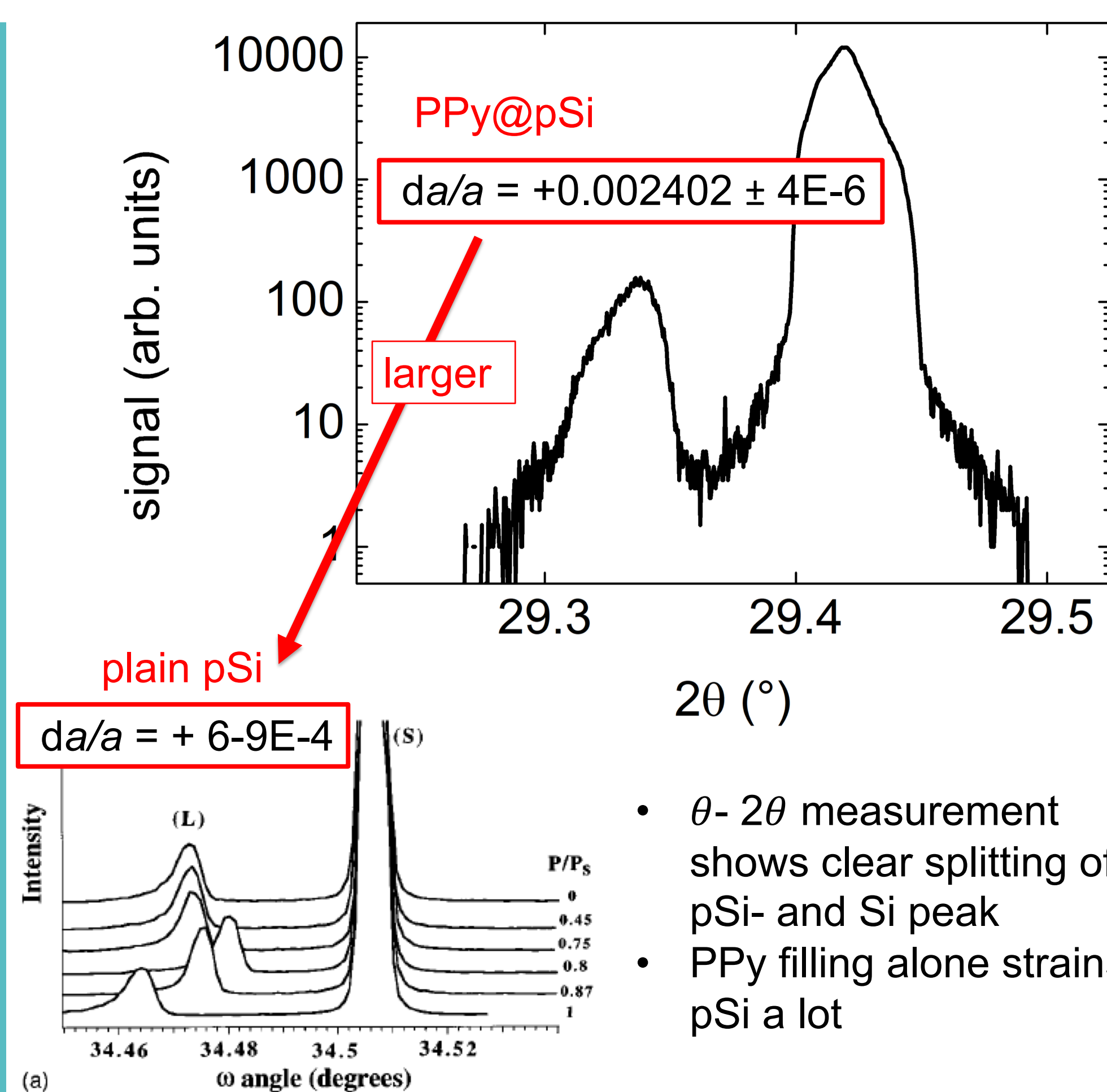
In-situ X-ray diffraction study of electrosorption-induced actuation in porous silicon

- polypyrrole (PPy) actuation:
 - expansion by intake of ions
 - contraction by release of ions
- Infiltrate pores of pSi with PPy, infiltrate with electrolyte, apply potential \rightarrow actuator



- θ - 2θ - measurement: Bragg diffraction on both pSi and bulk Si.
- Lattice mismatch of pSi:

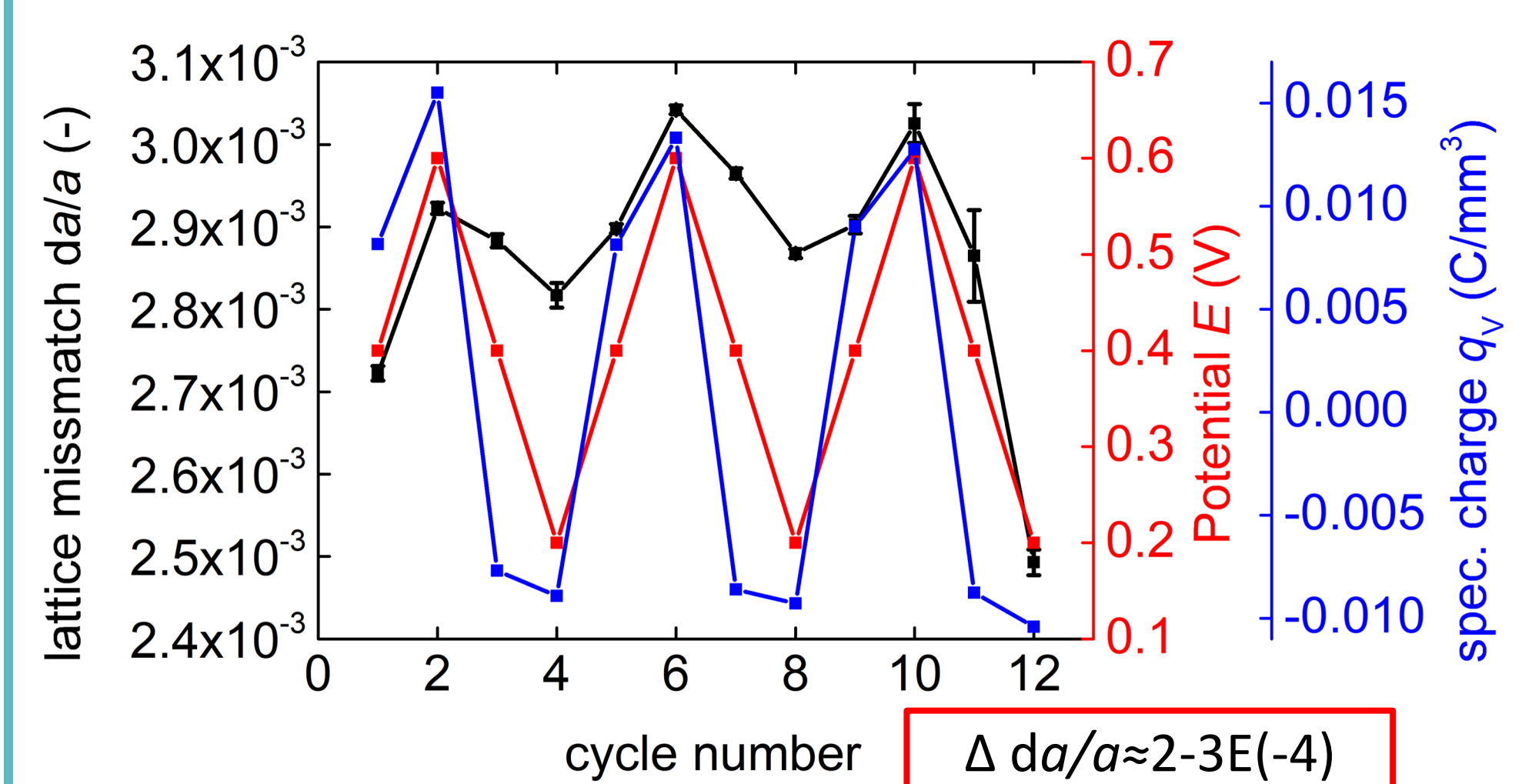
$$\frac{\partial a}{a} = \frac{\theta_{pSi} - \theta_{Si}}{\tan(\theta_{Si})} = \frac{\partial \theta}{\tan(\theta_{Si})}$$



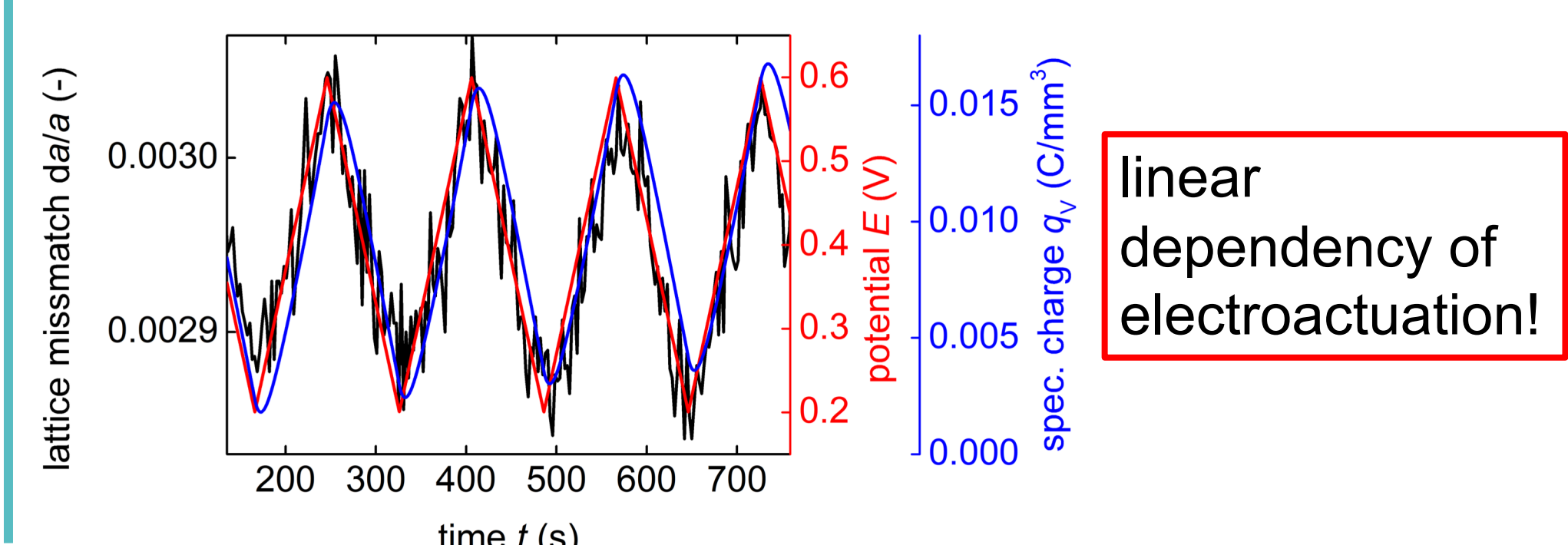
Dolino, G., Bellet, D. and Faivre, C. (1996). Adsorption strains in porous silicon. *Phys. Rev. B*, 54(24), 17919.

- θ - 2θ measurement shows clear splitting of pSi- and Si peak
- PPy filling alone strains pSi a lot

voltage control of lattice mismatch:



- lattice **expands** when voltage is **increased**
- lattice **contracts** when voltage is **decreased**



linear dependency of electroactuation!